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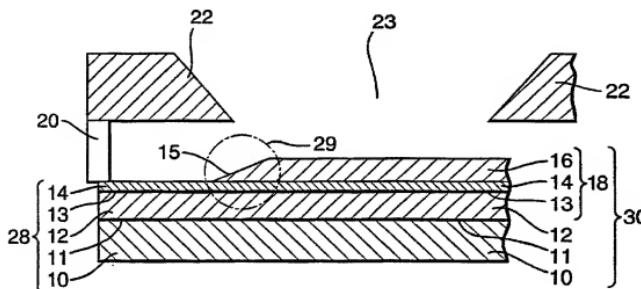
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(54) Title: METHOD OF FABRICATING A SEMICONDUCTOR DEVICE



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(57) Abstract: A method of fabricating a semiconductor device includes a step of growing at least one tapered epitaxial layer upon a supporting surface by chemical beam epitaxy, the plane of the taper being inclined to the supporting surface.